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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Chen et al.

Serial No.: 09/748,256

Group Art Unit: 2811

Filed: December 27, 2000

Examiner: Ori Nadav

For: SEMICONDUCTOR DEVICE ON A COMBINATION BULK SILICON AND  
SILICON ON INSULATOR (SOI) SUBSTRATE

Honorable Assistant Commissioner of Patents

Washington, D.C. 20231

BOX AF

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FJONES

11-9-01

J. Jones  
11/28/01AMENDMENT UNDER 37 C.F.R. §1.116

Sir:

In response to the Office Action dated August 14, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims as follows:

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on
29. (Amended) A semiconductor device comprising:  
a bulk silicon region comprising bulk silicon;  
a silicon-on-insulator (SOI) region comprising an insulator layer formed in said bulk silicon;  
a crystallized silicon layer formed on said bulk silicon and said insulator layer by annealing amorphous silicon and having isolation trenches formed therein so as to remove defective regions; and  
isolation oxides formed in said isolation trenches.

31. (Amended) The semiconductor device according to claim 30, wherein said insulator layer comprises an oxide layer.

34. (Amended) The semiconductor device according to claim 31, wherein said isolation